

PSMN1R1-40BS

N-channel 40 V 1.3 m Ω standard level MOSFET in D2PAK Rev. 2 — 29 February 2012 Product data

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel MOSFET in D2PAK (SOT404) package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC convertors
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	N	Viin	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-		-	40	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1] _	•	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	•	-	306	W
Tj	junction temperature		-	55	-	175	°C
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 °C;$ see Figure 12;see Figure 13	-	•	1.68	2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	•	1.16	1.3	mΩ
Dynamic char	acteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A}; V_{DS} = 20 \text{ V};$	-		32	-	nC
Q _{G(tot)}	total gate charge	see Figure 14;see Figure 15	-	•	136	-	nC
Avalanche rug	ggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} &V_{GS}=10 \text{ V; } T_{j(init)}=25 \text{ °C; } I_D=120 \text{ A;} \\ &V_{sup} \leq 40 \text{ V; unclamped; } R_{GS}=50 \Omega; \\ &t_p=0.1 \text{ ms} \end{split}$	-	•	-	1.4	J

[1] Continuous current is limited by package



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	•	
2	D	drain[1]	mb	D
3	S	source		
mb	D	drain	1	G (F)
				mbb076 S
			∐ ∐ 1 3	
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R1-40BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

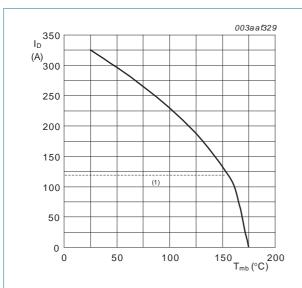
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
_						
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	40	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	40	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C	<u>[1]</u>	-	120	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3		-	1320	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-di	rain diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1320	Α
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le$ 40 V; unclamped; R_{GS} = 50 Ω ; t_p = 0.1 ms		-	1.4	J

^[1] Continuous current is limited by package.

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 $V_{GS} \ge 10 \text{ V}$; (1) Capped at 120 A due to package

Fig 1. Normalized continuous drain current as a function of mounting base temperature

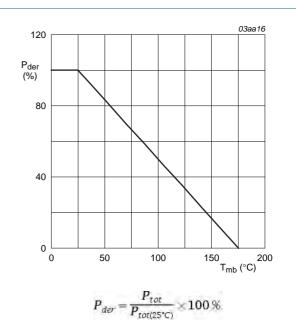
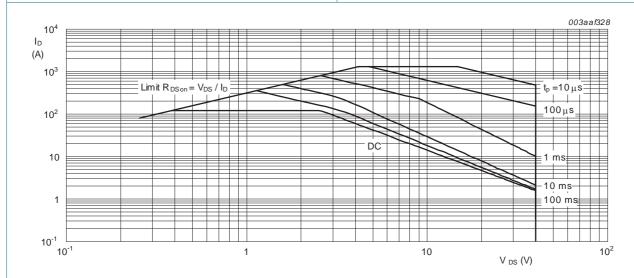


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 T_{mb} = 25 °C; I_{DM} is a single pulse; Capped at 120 A due to package

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.49	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

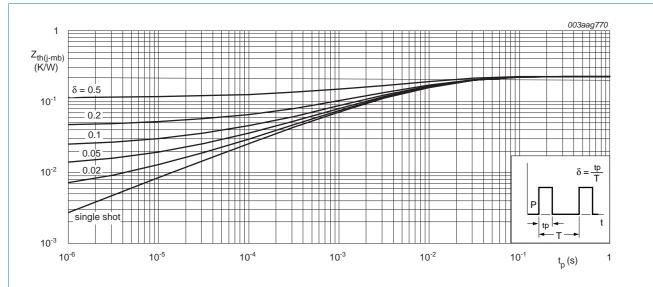


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Cumb al	Characteristics	Canditions	A4!	T	NA	11!4
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	racteristics	1 050 A V 0 V T 55.00				
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 V; T_j = 25 ^{\circ}\text{C}$	40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 10	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 11</u> ;see <u>Figure 10</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see Figure 12;see Figure 13	-	1.68	2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12;see Figure 13	-	2.3	2.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	1.16	1.3	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	1.1	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	133	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$	-	136	-	nC
Q _{GS}	gate-source charge	see Figure 14;see Figure 15	-	52	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	30	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	22	-	nC
Q _{GD}	gate-drain charge		-	32	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 75 A; V _{DS} = 20 V;see <u>Figure 14</u> ; see Figure 15	-	6.1	-	V
C _{iss}	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9710	-	pF
C _{oss}	output capacitance	T _j = 25 °C;see <u>Figure 16</u>	-	2042	-	pF
C _{rss}	reverse transfer capacitance		-	994	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 0.8 \Omega; V_{GS} = 5 \text{ V};$	-	45	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	66	-	ns
t _{d(off)}	turn-off delay time		-	111	-	ns
t _f	fall time		-	53	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	n diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	64	-	ns
Q _r	recovered charge	$V_{DS} = 20 \text{ V}$	-	117	-	nC

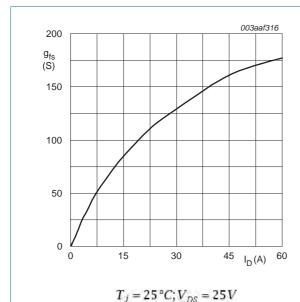


Fig 5. Forward transconductance as a function of drain current; typical values

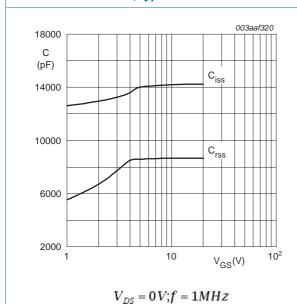
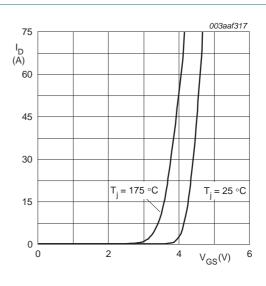


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



$$V_{DS} > I_D \times R_{DSon}$$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

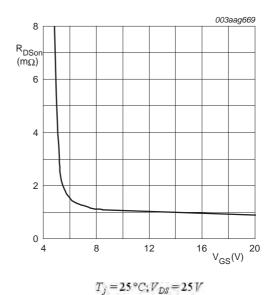


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

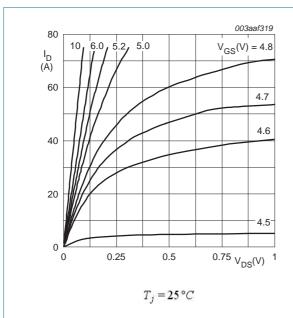


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

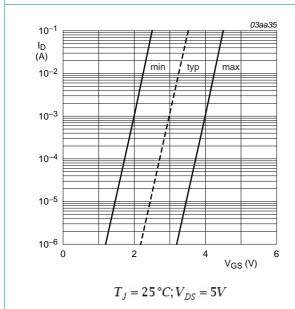
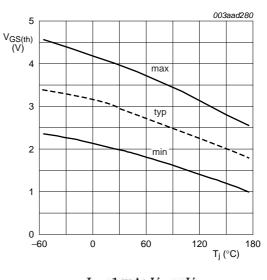


Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

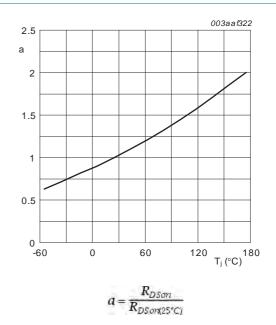


Fig 12. Normalized drain-source on state resistance factor as a function of junction temperature

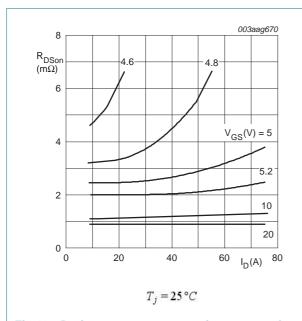


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

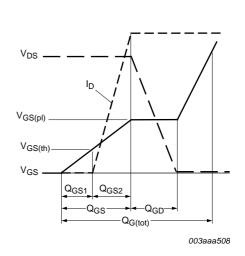


Fig 14. Gate charge waveform definitions

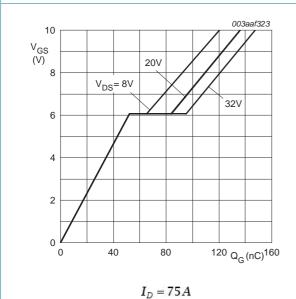
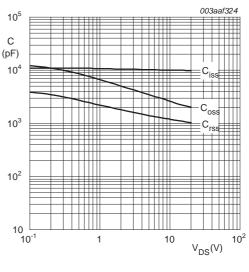
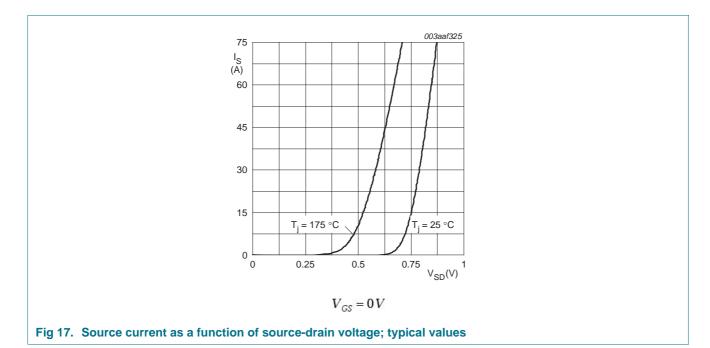


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline

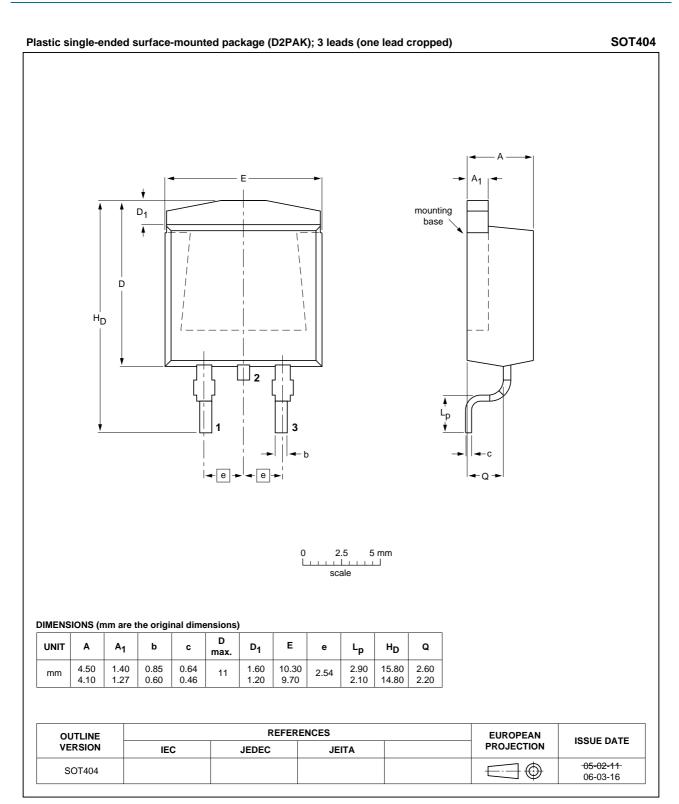


Fig 18. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R1-40BS v.2	20120229	Product data sheet	-	PSMN1R1-40BS v.1
Modifications:	 Status changed free 	om objective to product.		
	 Various changes t 	o content.		
PSMN1R1-40BS v.1	20110929	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PSMN1R1-40BS

Nexperia

N-channel 40 V 1.3 m Ω standard level MOSFET in D2PAK

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